International
IOR Rectifier

IRF6709S2TRPbF
IRF6709S2TR1PbF

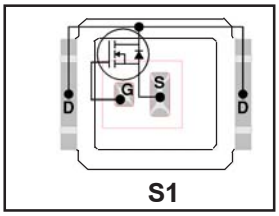
DirectFET™ Power MOSFET ②

- RoHS Compliant and Halogen Free ①
- Low Profile (<0.7 mm)
- Dual Sided Cooling Compatible ①
- Ultra Low Package Inductance
- Optimized for High Frequency Switching ①
- Ideal for CPU Core DC-DC Converters
- Optimized for Control FET Application ①
- Compatible with existing Surface Mount Techniques ①
- 100% Rg tested

Typical values (unless otherwise specified)

V_{DSS}	V_{GS}	$R_{DS(on)}$	$R_{DS(on)}$
25V max	±20V max	5.9mΩ@10V	10.1mΩ@4.5V

$Q_{g\ tot}$	Q_{gd}	Q_{gs2}	Q_{rr}	Q_{oss}	$V_{gs(th)}$
8.1nC	2.8nC	1.1nC	9.3nC	4.6nC	1.8V



S1

DirectFET™ ISOMETRIC

Applicable DirectFET Outline and Substrate Outline ①

S1	S2	SB		M2	M4		L4	L6	L8	

Description

The IRF6709S2TRPbF combines the latest HEXFET® Power MOSFET Silicon technology with the advanced DirectFET™ packaging to achieve improved performance in a package that has the footprint of a MICRO-8 and only 0.7 mm profile. The DirectFET package is compatible with existing layout geometries used in power applications, PCB assembly equipment and vapor phase, infra-red or convection soldering techniques, when application note AN-1035 is followed regarding the manufacturing methods and processes. The DirectFET package allows dual sided cooling to maximize thermal transfer in power systems, improving previous best thermal resistance by 80%.

The IRF6709S2TRPbF has low charge along with ultra low package inductance providing significant reduction in switching losses. The reduced losses make this product ideal for high efficiency DC-DC converters that power the latest generation of processors operating at higher frequencies. The IRF6709S2TRPbF has been optimized for the control FET socket of synchronous buck operating from 12 volt bus converters.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	25	V
V_{GS}	Gate-to-Source Voltage	±20	
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V ③	12	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V ③	9.7	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V ④	39	
I_{DM}	Pulsed Drain Current ⑤	100	
E_{AS}	Single Pulse Avalanche Energy ⑥	51	mJ
I_{AR}	Avalanche Current ⑤	10	A

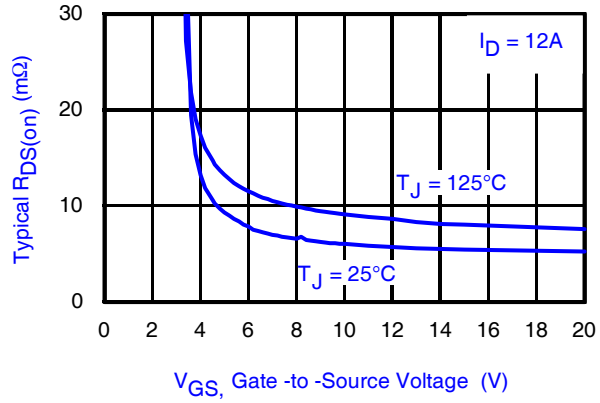


Fig 1. Typical On-Resistance vs. Gate Voltage

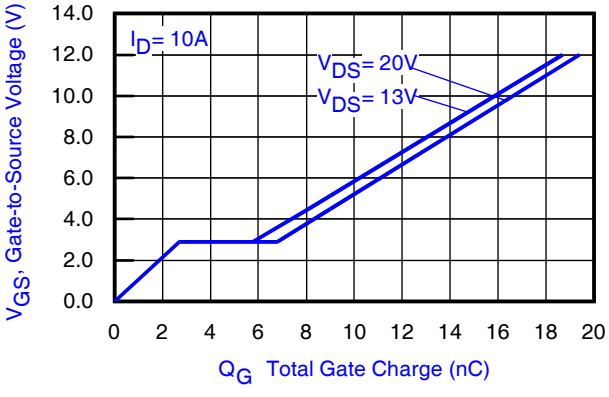


Fig 2. Typical Total Gate Charge vs Gate-to-Source Voltage

Notes:

① Click on this section to link to the appropriate technical paper.
② Click on this section to link to the DirectFET Website.
③ Surface mounted on 1 in. square Cu board, steady state.
④ T_C measured with thermocouple mounted to top (Drain) of part.
⑤ Repetitive rating; pulse width limited by max. junction temperature.
⑥ Starting T_J = 25°C, L = 1.02mH, R_G = 25Ω, I_{AS} = 10A.

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	25	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	19	—	mV/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	5.9	7.8	mΩ	V_{GS} = 10V, I_D = 12A ⑦
		—	10.1	13.5		V_{GS} = 4.5V, I_D = 10A ⑦
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.8	2.35	V	V_{DS} = V_{GS}, I_D = 25µA
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-7.2	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	µA	V_{DS} = 20V, V_{GS} = 0V
		—	—	150		V_{DS} = 20V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
gfs	Forward Transconductance	19	—	—	S	V_{DS} = 13V, I_D =10A
Q_g	Total Gate Charge	—	8.1	12		
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	1.9	—		V_{DS} = 13V
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	1.1	—	nC	V_{GS} = 4.5V
Q_{gd}	Gate-to-Drain Charge	—	2.8	—		I_D = 10A
Q_{godr}	Gate Charge Overdrive	—	2.3	—		See Fig. 18
Q_{sw}	Switch Charge (Q_{gs2} + Q_{gd})	—	3.9	—		
Q_{oss}	Output Charge	—	4.6	—	nC	V_{DS} = 10V, V_{GS} = 0V
R_G	Gate Resistance	—	3.2	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	8.4	—		V_{DD} = 13V, V_{GS} = 4.5V ⑦
t_r	Rise Time	—	25	—		I_D = 10A
$t_{d(off)}$	Turn-Off Delay Time	—	9.1	—	ns	R_G= 6.2Ω
t_f	Fall Time	—	9.5	—		
C_{iss}	Input Capacitance	—	1010	—		V_{GS} = 0V
C_{oss}	Output Capacitance	—	340	—	pF	V_{DS} = 13V
C_{rss}	Reverse Transfer Capacitance	—	140	—		f = 1.0MHz

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	26	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ⑤	—	—	100		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	T_J = 25°C, I_S = 10A, V_{GS} = 0V ⑦
t_{rr}	Reverse Recovery Time	—	15	23	ns	T_J = 25°C, I_F =10A
Q_{rr}	Reverse Recovery Charge	—	9.3	14	nC	di/dt = 200A/µs ⑦

Notes:

⑤ Repetitive rating; pulse width limited by max. junction temperature.

⑦ Pulse width ≤ 400µs; duty cycle ≤ 2%.

Absolute Maximum Ratings

	Parameter	Max.	Units
P_D @T_A = 25°C	Power Dissipation ③	1.8	W
P_D @T_A = 70°C	Power Dissipation ③	1.3	
P_D @T_C = 25°C	Power Dissipation ④	21	
T_P	Peak Soldering Temperature	270	°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③⑩	—	82	°C/W
$R_{\theta JA}$	Junction-to-Ambient ⑧⑩	12.5	—	
$R_{\theta JA}$	Junction-to-Ambient ⑨⑩	20	—	
$R_{\theta JC}$	Junction-to-Case ④⑩	—	7.2	
$R_{\theta J\text{-}PCB}$	Junction-to-PCB Mounted	1.0	—	
	Linear Derating Factor ③	0.012		W/°C

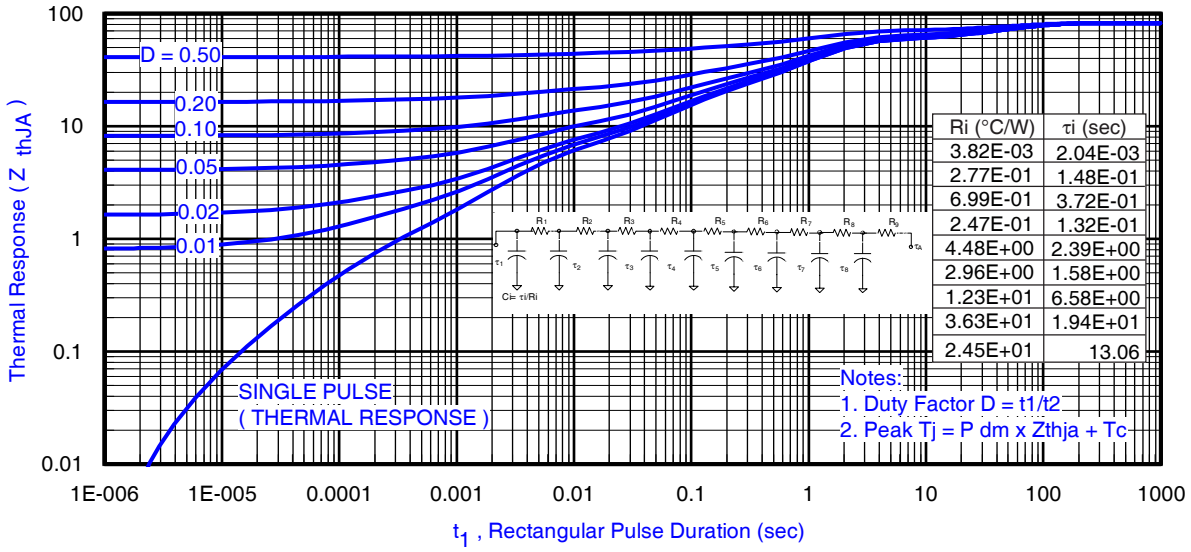


Fig 3. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient ①
(At lower pulse widths Zth_{JA} & Zth_{JC} are combined)

Notes:

③ Surface mounted on 1 in. square Cu board, steady state.

④ T_C measured with thermocouple incontact with top (Drain) of part.

⑧ Used double sided cooling, mounting pad with large heatsink.

⑨ Mounted on minimum footprint full size board with metalized back and with small clip heatsink.

⑩ R_θ is measured at T_J of approximately 90°C.

③ Surface mounted on 1 in. square Cu board (still air).

⑨ Mounted on minimum footprint full size board with metalized back and with small clip heatsink. (still air)

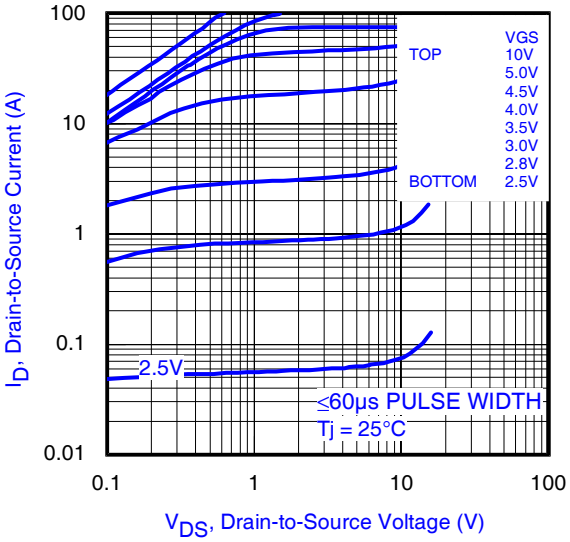


Fig 4. Typical Output Characteristics

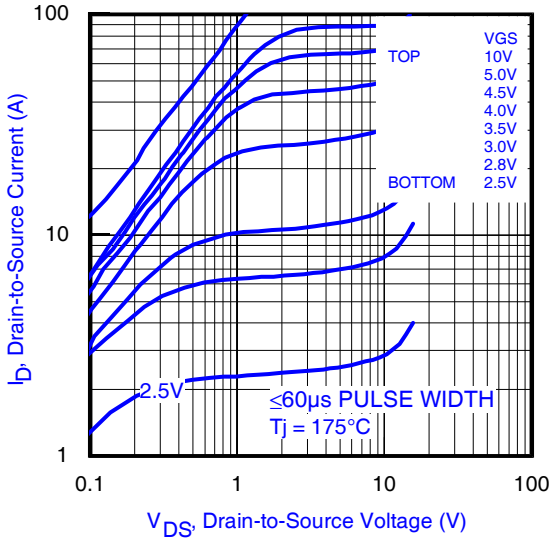


Fig 5. Typical Output Characteristics

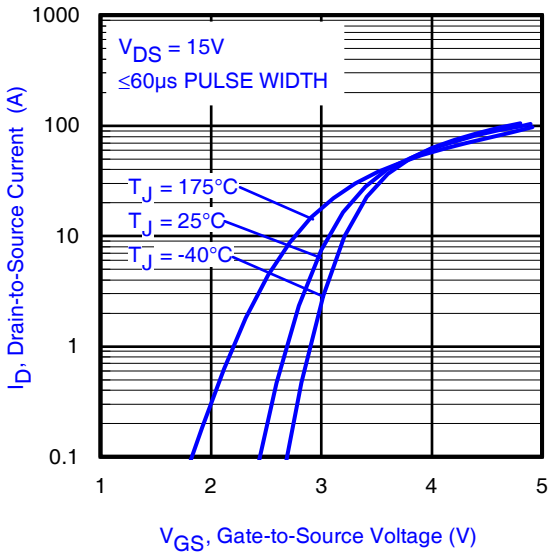


Fig 6. Typical Transfer Characteristics

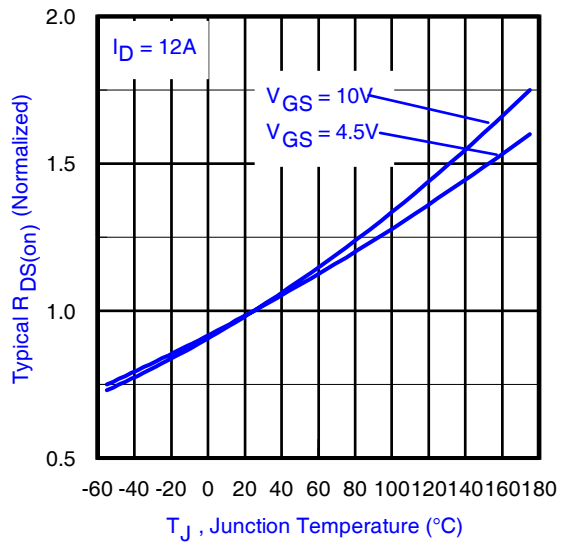


Fig 7. Normalized On-Resistance vs. Temperature

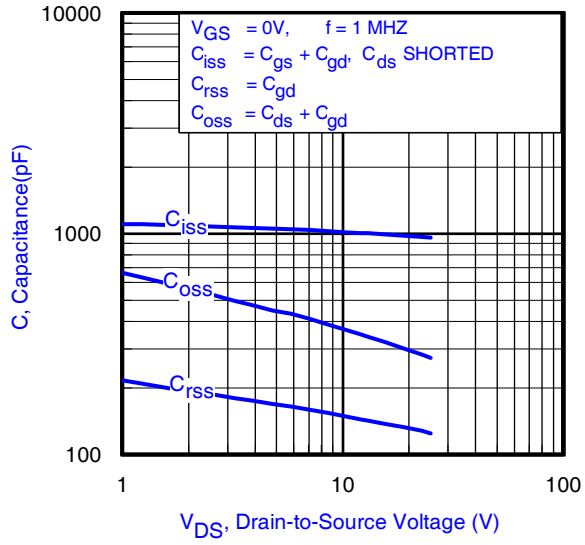


Fig 8. Typical Capacitance vs.Drain-to-Source Voltage

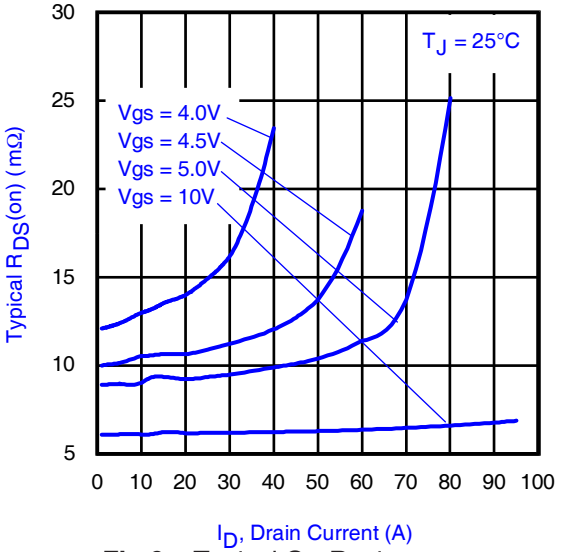


Fig 9. Typical On-Resistance vs. Drain Current and Gate Voltage

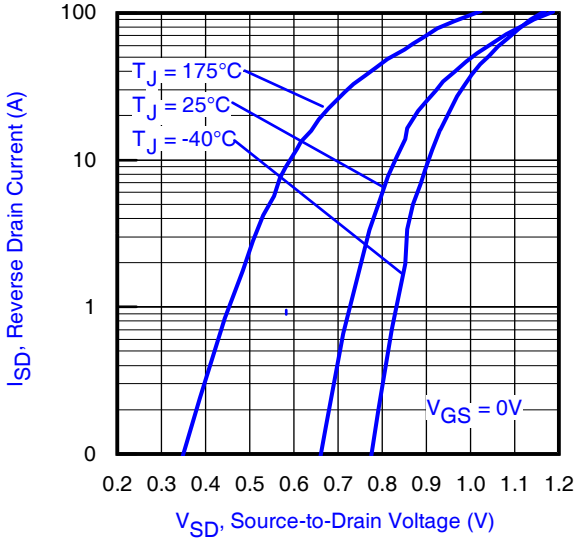


Fig 10. Typical Source-Drain Diode Forward Voltage

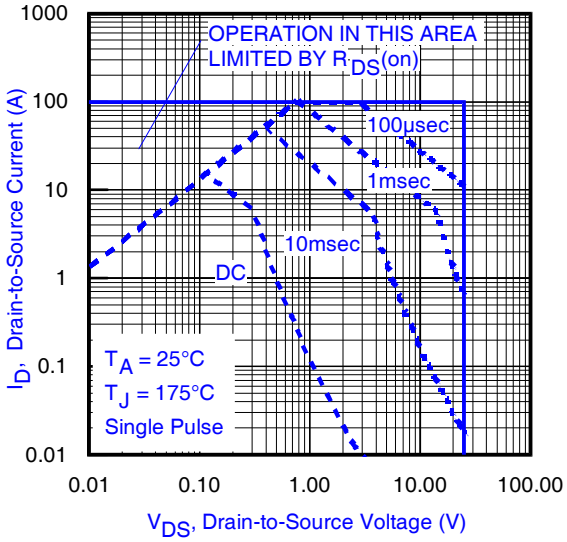


Fig 11. Maximum Safe Operating Area

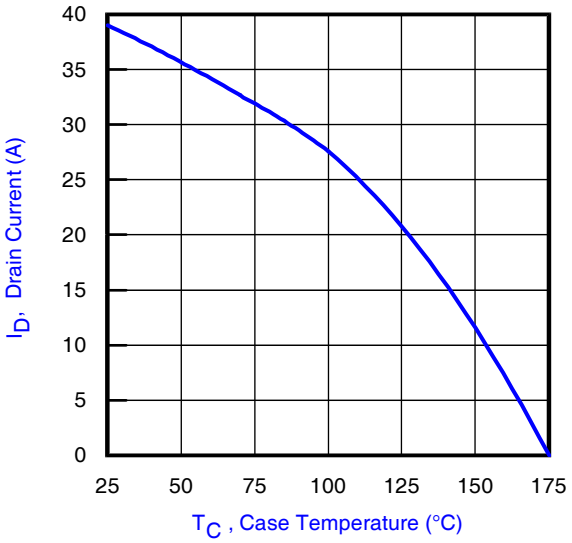


Fig 12. Maximum Drain Current vs. Case Temperature

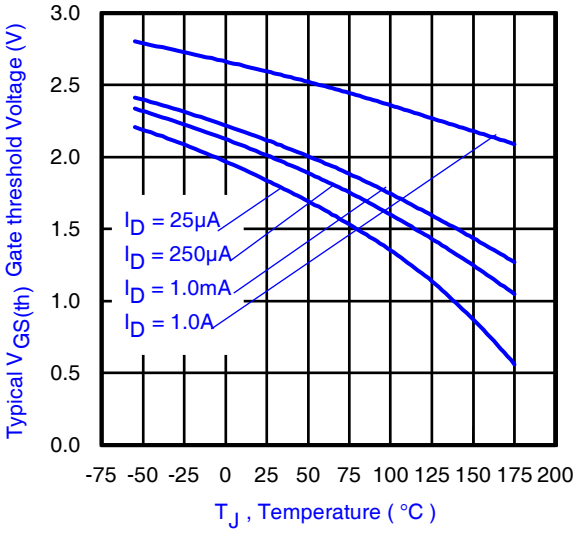


Fig 13. Typical Threshold Voltage vs. Junction Temperature

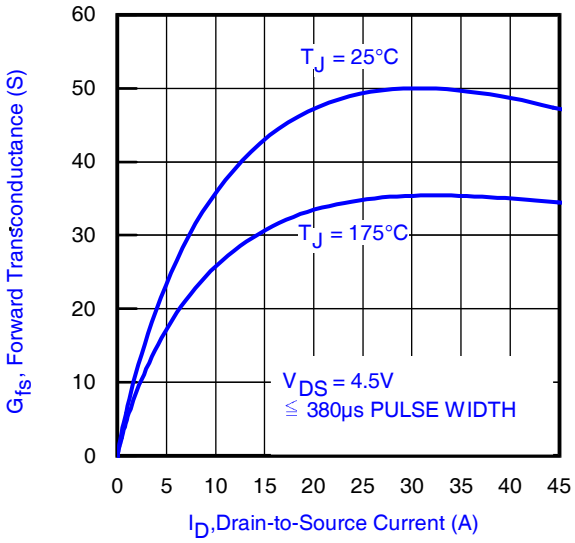


Fig 14. Typ. Forward Transconductance vs. Drain Current

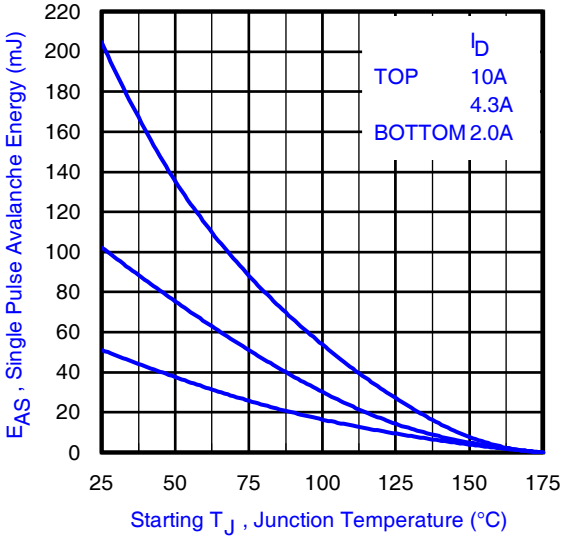


Fig 15. Maximum Avalanche Energy vs. Drain Current

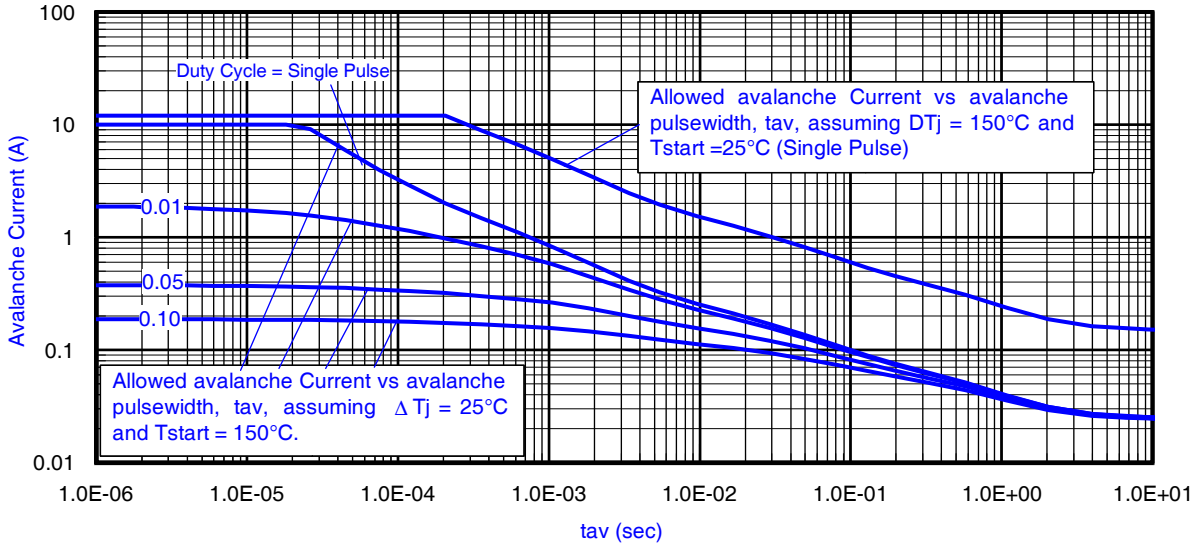


Fig 16. Typical Avalanche Current Vs.Pulsewidth

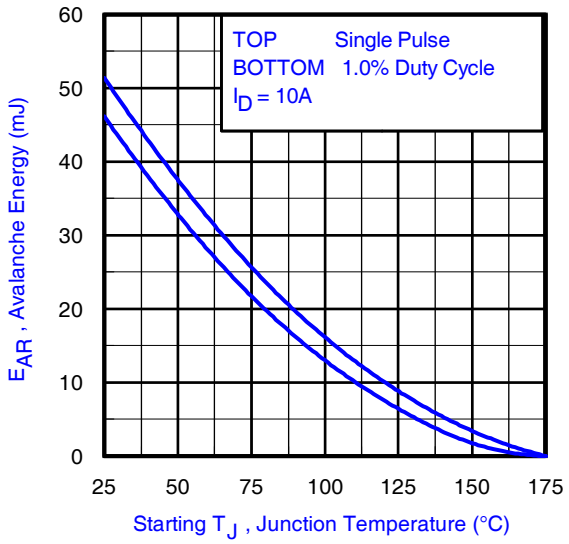


Fig 17. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 16, 17:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
   Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long asT_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 19a, 19b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 16, 17).
   t_{av} = Average time in avalanche.
   D = Duty cycle in avalanche = $t_{av} \cdot f$
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D\ (ave)} = 1/2\ (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$
$$E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}$$

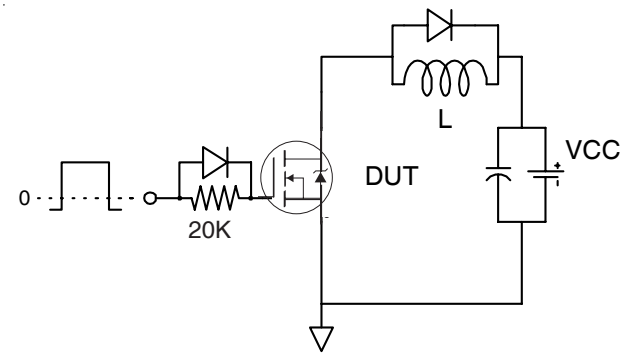


Fig 18a. Gate Charge Test Circuit

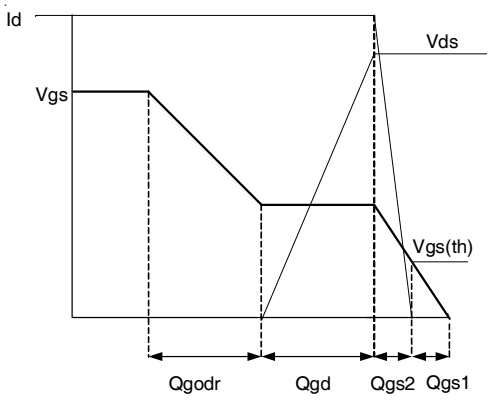


Fig 18b. Gate Charge Waveform

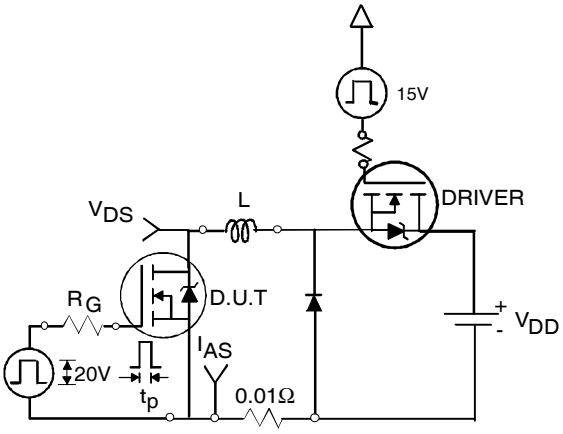


Fig 19a. Unclamped Inductive Test Circuit

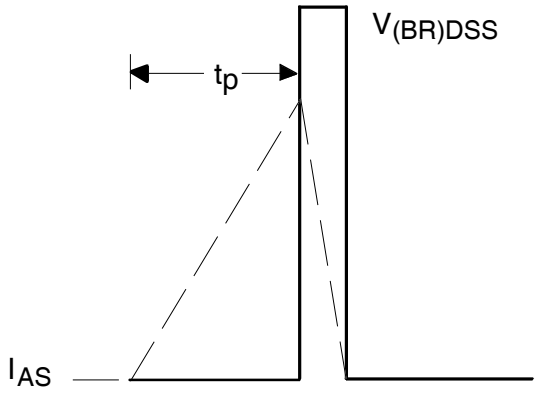


Fig 19b. Unclamped Inductive Waveforms

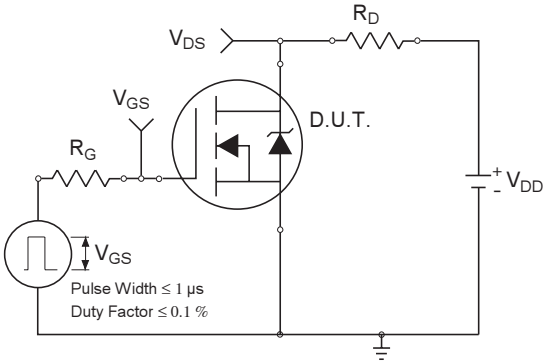


Fig 20a. Switching Time Test Circuit

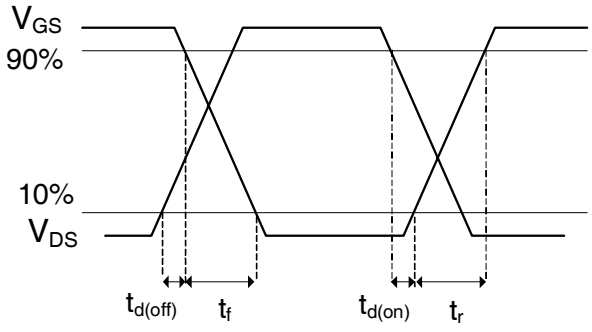


Fig 20b. Switching Time Waveforms

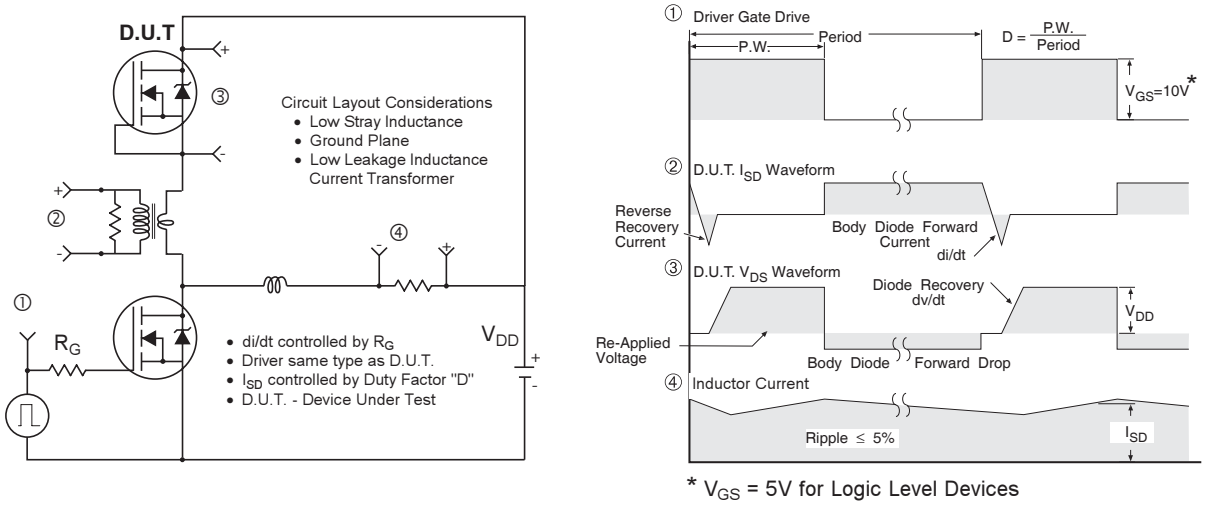
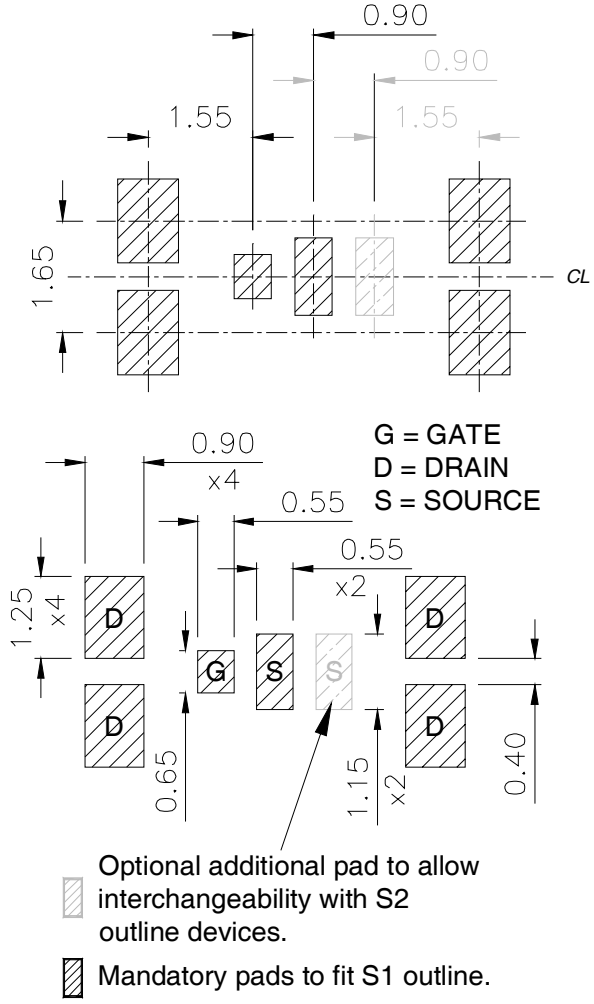


Fig 19. Diode Reverse Recovery Test Circuit for N-Channel HEXFET® Power MOSFETs

DirectFET™ Board Footprint, S1 Outline (Small Size Can).

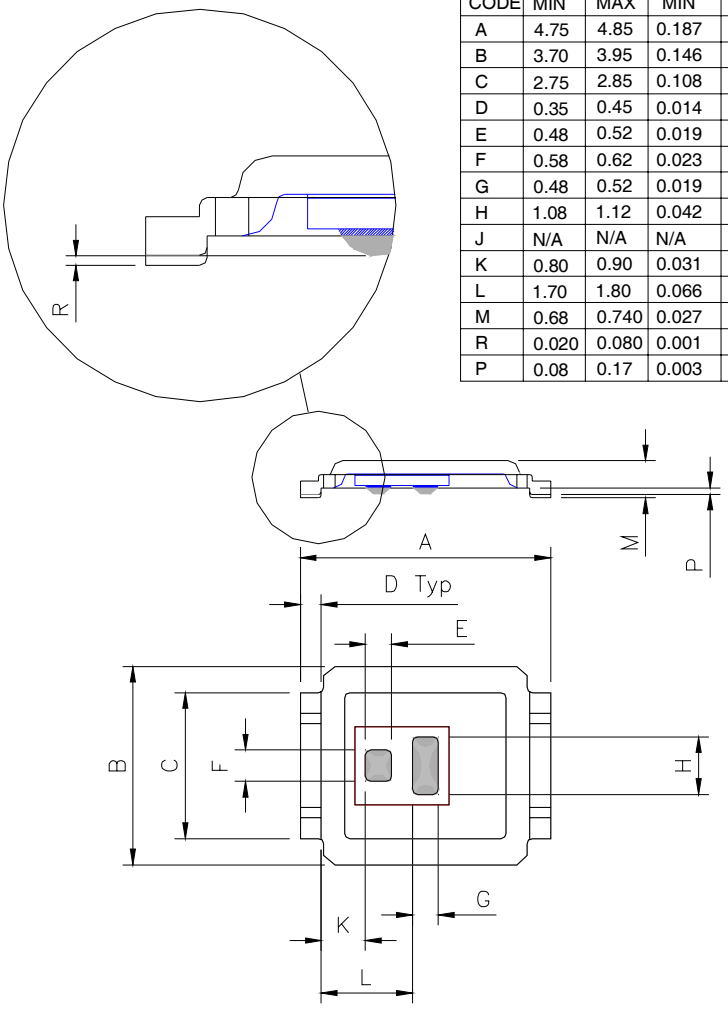
Please see DirectFET application note AN-1035 for all details regarding the assembly of DirectFET.
This includes all recommendations for stencil and substrate designs.



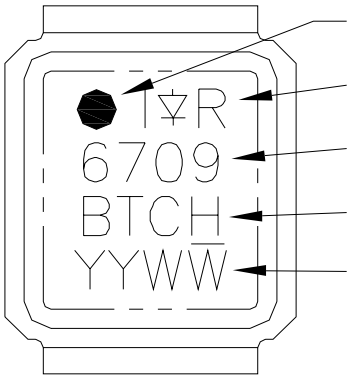
DirectFET™ Outline Dimension, S1 Outline (Small Size Can).

Please see AN-1035 for DirectFET assembly details and stencil and substrate design recommendations

DIMENSIONS				
	METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX
A	4.75	4.85	0.187	0.191
B	3.70	3.95	0.146	0.156
C	2.75	2.85	0.108	0.112
D	0.35	0.45	0.014	0.018
E	0.48	0.52	0.019	0.020
F	0.58	0.62	0.023	0.024
G	0.48	0.52	0.019	0.020
H	1.08	1.12	0.042	0.044
J	N/A	N/A	N/A	N/A
K	0.80	0.90	0.031	0.035
L	1.70	1.80	0.066	0.070
M	0.68	0.740	0.027	0.029
R	0.020	0.080	0.001	0.003
P	0.08	0.17	0.003	0.007



DirectFET™ Part Marking



GATE MARKING

LOGO

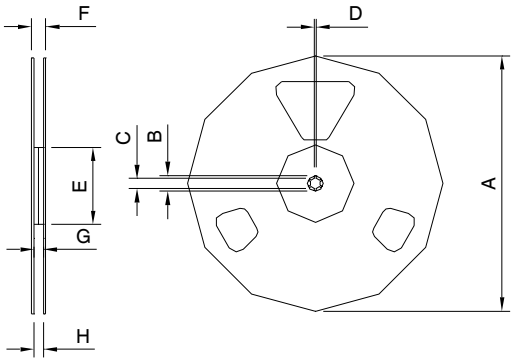
PART NUMBER

BATCH NUMBER

DATE CODE

Line above the last character of
the date code indicates "Lead-Free"

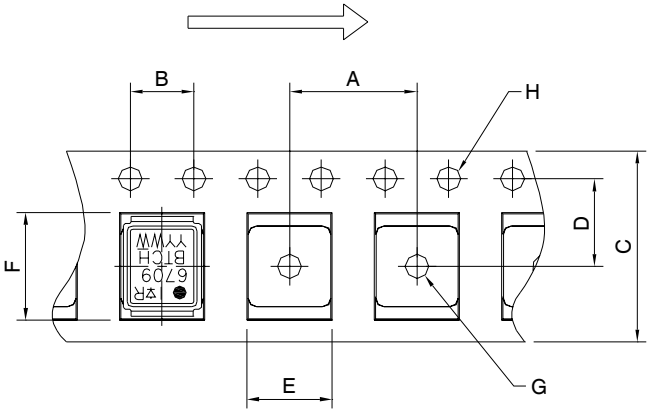
DirectFET™ Tape & Reel Dimension (Showing component orientation).



NOTE: Controlling dimensions in mm
Std reel quantity is 4800 parts. (ordered as IRF09S2TRPBF). For 1000 parts on 7" reel, order IRF6709S2MTR1PBF

REEL DIMENSIONS								
STANDARD OPTION **(QTY 4800)**					TR1 OPTION **(QTY 1000)**			
	METRIC		IMPERIAL		METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX
A	330.0	N.C	12.992	N.C	177.77	N.C	6.9	N.C
B	20.2	N.C	0.795	N.C	19.06	N.C	0.75	N.C
C	12.8	13.2	0.504	0.520	13.5	12.8	0.53	0.50
D	1.5	N.C	0.059	N.C	1.5	N.C	0.059	N.C
E	100.0	N.C	3.937	N.C	58.72	N.C	2.31	N.C
F	N.C	18.4	N.C	0.724	N.C	13.50	N.C	0.53
G	12.4	14.4	0.488	0.567	11.9	12.01	0.47	N.C
H	11.9	15.4	0.469	0.606	11.9	12.01	0.47	N.C

LOADED TAPE FEED DIRECTION



NOTE: CONTROLLING DIMENSIONS IN MM

DIMENSIONS				
	METRIC		IMPERIAL	
CODE	MIN	MAX	MIN	MAX
A	7.90	8.10	0.311	0.319
B	3.90	4.10	0.154	0.161
C	11.90	12.30	0.469	0.484
D	5.45	5.55	0.215	0.219
E	5.10	5.30	0.201	0.209
F	6.50	6.70	0.256	0.264
G	1.50	N.C	0.059	N.C
H	1.50	1.60	0.059	0.063

Data and specifications subject to change without notice.
This product has been designed and qualified to MSL1 rating for the Consumer market.
Additional storage requirement details for DirectFET products can be found in application note AN1035 on IR's Web site.
Qualification Standards can be found on IR's Web site.

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information.04/2009

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by Infineon ***manufacturer:***

Other Similar products are found below :

614233C 648584F MCH3443-TL-E MCH6422-TL-E FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI